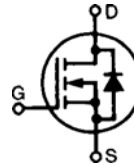


HiPerFET™ Power MOSFETs Q-Class

IXFK/IXFX 30N50Q
IXFK/IXFX 32N50Q

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , High dv/dt

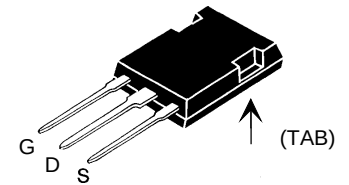


V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	30 A	0.16 Ω
500 V	32 A	0.15 Ω

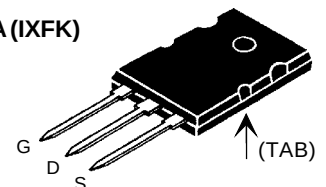
$$t_{rr} \leq 250 \text{ ns}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	30N50Q 30 32N50Q 32	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	30N50Q 120 32N50Q 128	A
I_{AR}	$T_C = 25^\circ\text{C}$	32	A
E_{AR}	$T_C = 25^\circ\text{C}$	45	mJ
E_{AS}		1500	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	416	W
T_J		-55 ... + 150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... + 150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

PLUS 247™
(IXFX)



TO-264 AA (IXFK)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- International standard packages
- Low $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

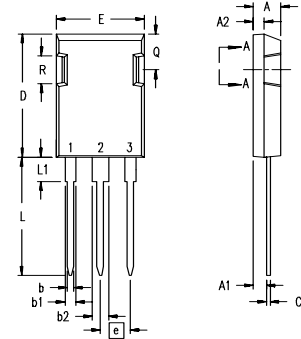
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$			100 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Note 1	32N50Q 30N50Q		0.15 Ω 0.16 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1	18	28	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3950	pF
C_{oss}			640	pF
C_{rss}			210	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External),		35	ns
t_r			42	ns
$t_{d(off)}$			75	ns
t_f			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		150	nC
Q_{gs}			26	nC
Q_{gd}			85	nC
R_{thJC}			0.3	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			32 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			128 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		0.75	ns
Q_{RM}				μC
I_{RM}			7.5	A

Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

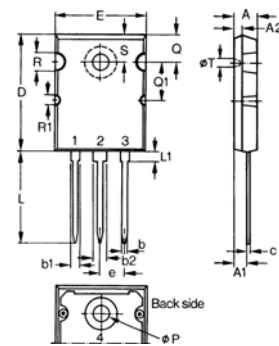
PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

Figure 1. Output Characteristics at 25°C

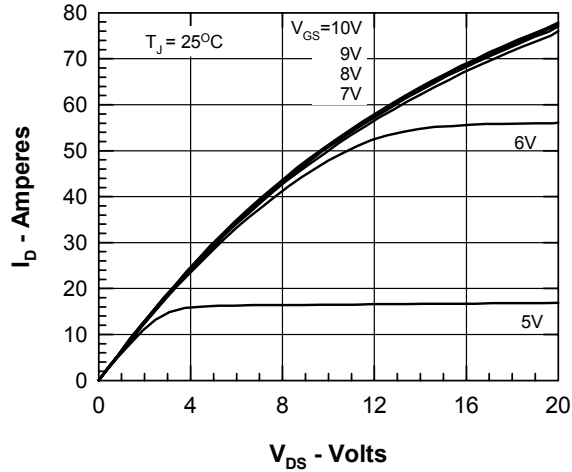


Figure 2. Output Characteristics at 125°C

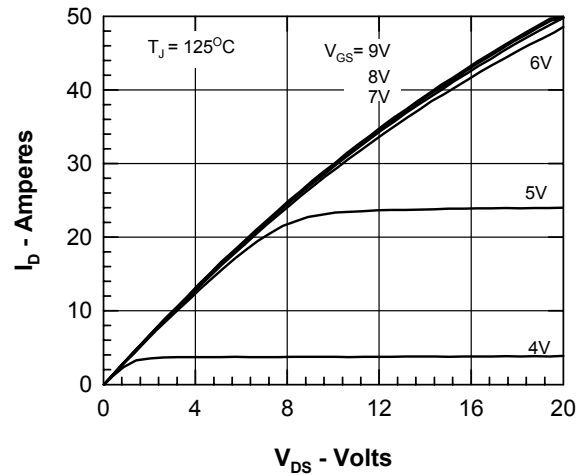


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

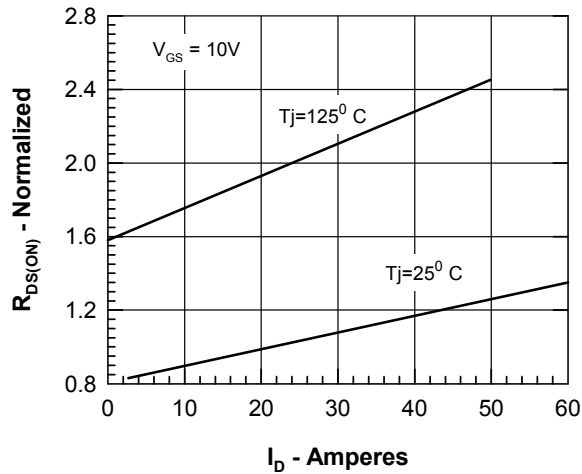


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J

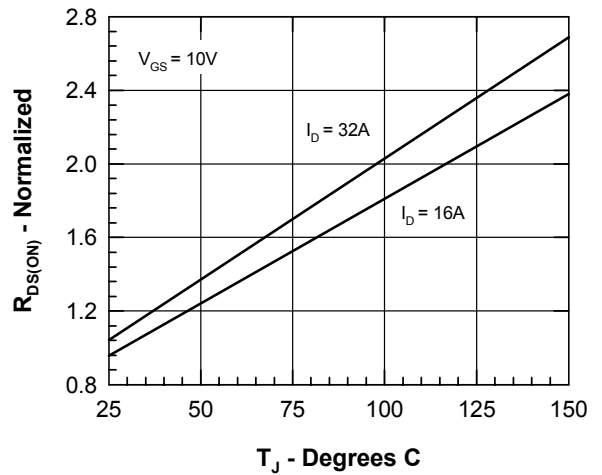


Figure 5. Drain Current vs. Case Temperature

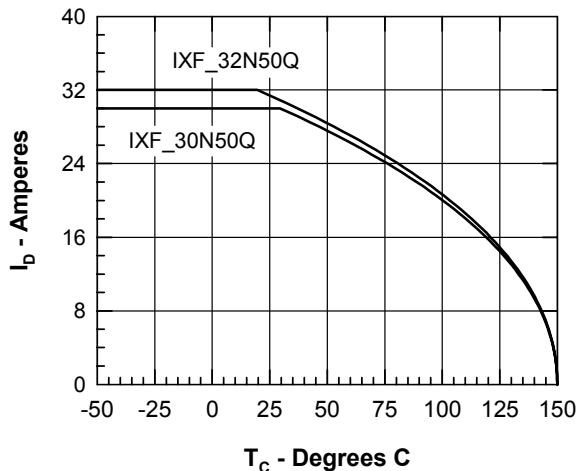


Figure 6. Admittance Curves

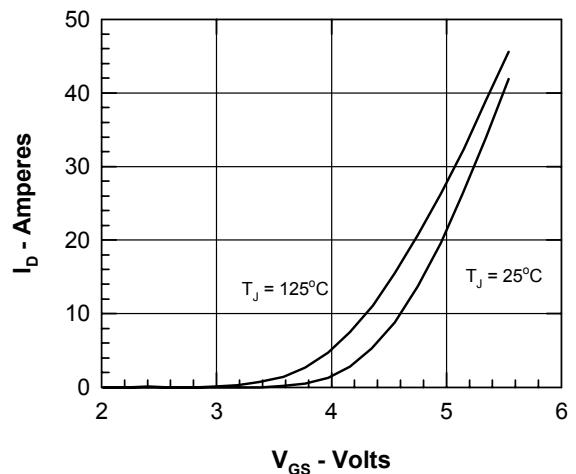


Figure 7. Gate Charge

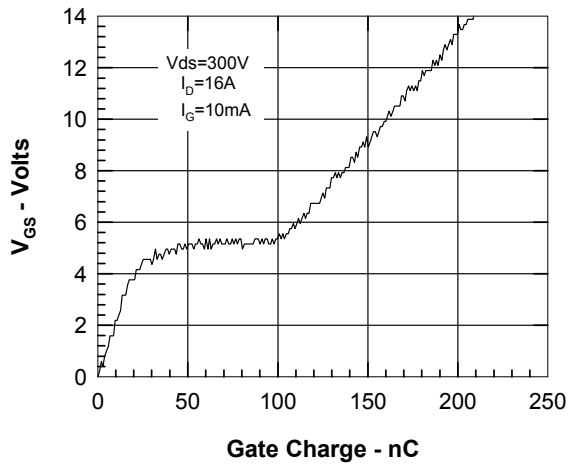


Figure 8. Capacitance Curves

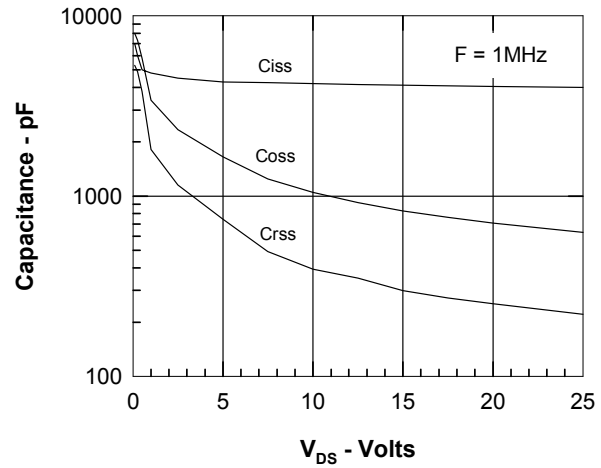


Figure 9. Forward Voltage Drop of the Intrinsic Diode

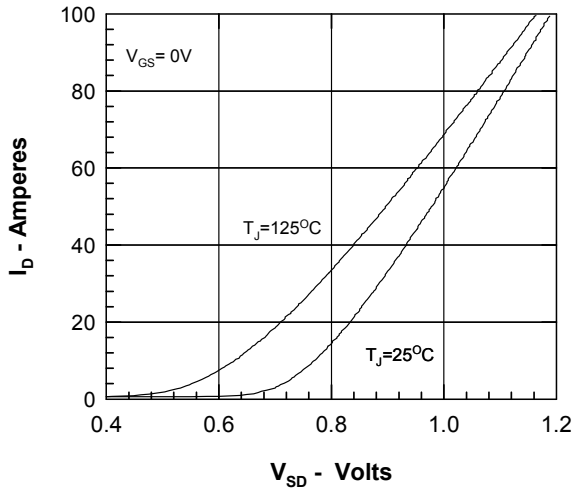


Figure 10. Transient Thermal Resistance

